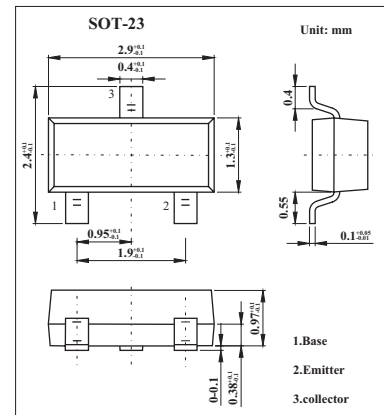


Medium Power Transistor

FMMTL718

■ Features

- Very low equivalent on-resistance; $R_{CE(sat)}=210\text{m}\Omega$ at 1.5A.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-20	V
Collector-emitter voltage	V_{CEO}	-20	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-1	A
Peak pulse current	I_{CM}	-2	A
Base current	I_B	-200	mA
Power dissipation	P_{tot}	-500	mW
Operating and storage temperature range	T_j, T_{stg}	-55 to +150	$^\circ\text{C}$

FMRTL718

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	IC=-100μA	-20	-65		V
Collector-emitter breakdown voltage	V(BR)CEO	IC=-10mA*	-20	-55		V
Emitter-base breakdown voltage	V(BR)EBO	IE=-100μA	-5	-8.8		V
Collector-base cut-off current	ICBO	VCE=-15V			-10	nA
Emitter-base current	IEBO	VEB=-4V			-10	nA
Collector-emitter saturation voltage	VCE(sat)	IC=-100mA, IB=-10mA* IC=-500mA, IB=-20mA* IC=-1A, IB=-50mA* IC=-1.5A, IB=-100mA		-33 -130 -230 -315	-50 -180 -320 -450	mV
Base-emitter saturation voltage	VBE(sat)	IC=-1.25A, IB=-100mA*		-950	-1100	mV
Base-emitter ON voltage	VBE(on)	IC=-1.25A, VCE=-2V*		-850	-1000	mV
DC current gain	hFE	IC=-10mA, VCE=-2V IC=-100mA, VCE=-2V* IC=-0.5A, VCE=-2V* IC=-1A, VCE=-2V* IC=-1.5A, VCE=-2V*	300 300 200 120 50	500 450 320 200 80		
Current-gain-bandwidth product	fT	IC=-50mA, VCE=-10V f=100MHz		265		MHz
Output capacitance	Cobo	VCE=-10V, f=1MHz		9	12	pF
Turn-on time	t(on)	IC=-1A, VCC=-10V		108		ns
Turn-off time	t(off)	IB1=IB2=-10mA		121		ns

* Pulse test: tp ≤ 300 μs; d ≤ 0.02.

■ Marking

Marking	L78
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